

TOSHIBA HIGH EFFICIENCY DIODE STACK (HED) SILICON EPITAXIAL TYPE

10DL2C48A, 10FL2C48A, U10DL2C48A, U10FL2C48A

SWITCHING TYPE POWER SUPPLY APPLICATION.

CONVERTER & CHOPPER APPLICATION.

- Repetitive Peak Reverse Voltage : V_{RRM} =200, 300V
- Average Output Rectified Current : I_O =10A
- Ultra Fast Reverse-Recovery Time : t_{rr} =35ns Max.
- Low Switching Losses and Output Noise.

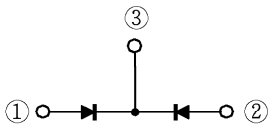
Unit in mm

10DL2C48A, 10FL2C48A		U10DL2C48A, U10FL2C48A	
JEDEC	—	JEDEC	—
EIAJ	—	EIAJ	—
TOSHIBA	12-10D1A	TOSHIBA	12-10D2A

MAXIMUM RATINGS

CHARACTERISTIC		SYMBOL	RATING	UNIT
Repetitive Peak Reverse Voltage	10DL2C48A	V _{RRM}	200	V
	U10DL2C48A			
	10FL2C48A			
	U10FL2C48A			
Average Output Rectified Current		I _O	10	A
Peak One Cycle Surge Forward Current		I _{FSM}	50 (50Hz)	A
			55 (60Hz)	
Junction Temperature		T _j	−40~150	℃
Storage Temperature Range		T _{stg}	−40~150	℃

POLARITY



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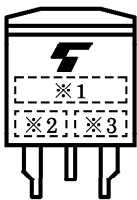
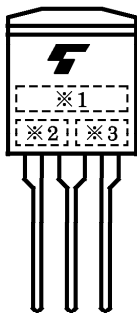
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ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Peak Forward Voltage	10DL2C48A	V _{FM}	I _{FM} = 5A	—	—	0.98	V
	U10DL2C48A			—	—	1.3	
	10FL2C48A			—	—	1.3	
	U10FL2C48A			—	—	1.3	
Repetitive Peak Reverse Current		I _{RRM}	V _{RRM} = Rated	—	—	10	μA
Reverse Recovery Time		t _{rr}	I _F = 2A, di / dt = − 20A / μs	—	—	35	ns
Forward Recovery Time		t _{fr}	I _F = 1A	—	—	100	ns
Thermal Resistance		R _{th(j-c)}	DC Total, Junction to Case	—	—	2.5	°C / W

V_{FM}, I_{RRM}, t_{rr}, t_{fr} : A Value of one cell.

MARKING



※ 1	MARK	10DL2C 10FL2C	TYPE	10DL2C48A, U10DL2C48A 10FL2C48A, U10FL2C48A
※ 2	A			
※ 3	Lot Number □□ — Month (Starting form Alphabet A) —— Year (Last Number of the Cristian Era)			

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